

描述 / Descriptions

SOT-23 塑封封装 N 沟道 MOS 场效应管。

N- CHANNEL MOSFET in a SOT-23 Plastic Package.

特征 / Features

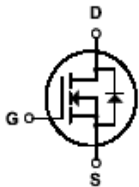
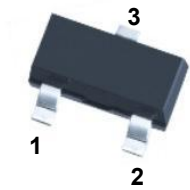
芯片采用超高密度元胞设计技术， $R_{DS(ON)}$ 导通电阻小，SOT-23 封装。

Super high dense cell design for low $R_{DS(ON)}$, SOT-23 package.

用途 / Applications

电池管理，高速开关，低功率 DC-DC 转换。

Battery management, High speed switch, low power DC to DC converter.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN 1 : G

PIN 2 : S

PIN 3 : D

印章代码 / Marking

Marking	A2H
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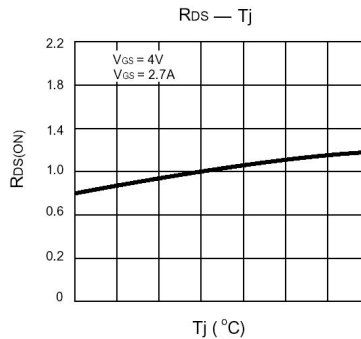
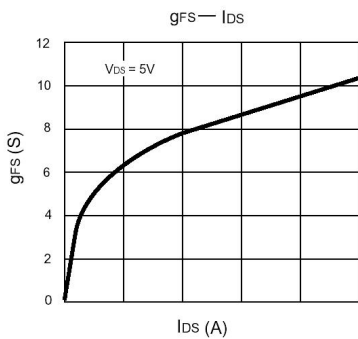
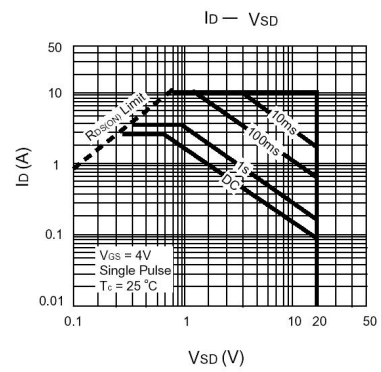
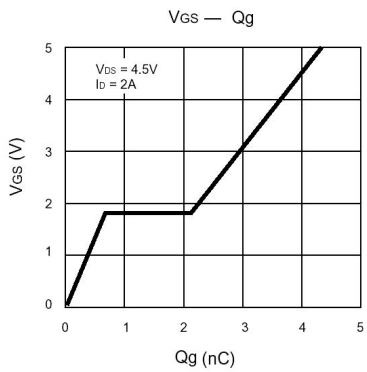
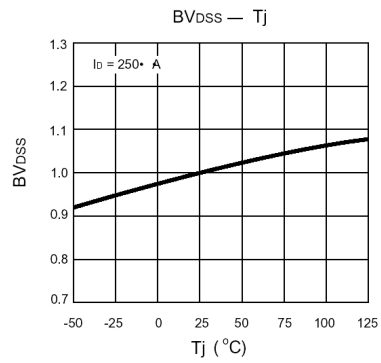
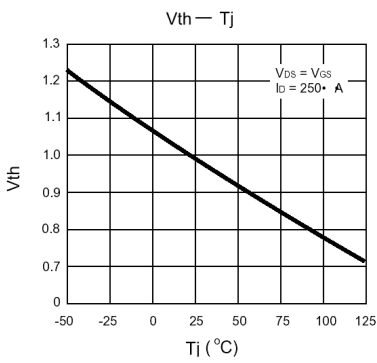
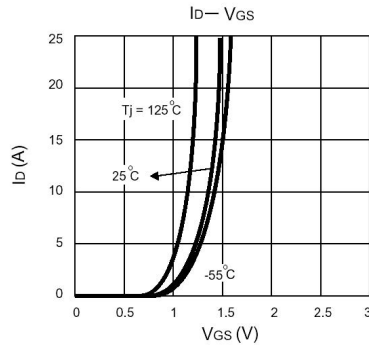
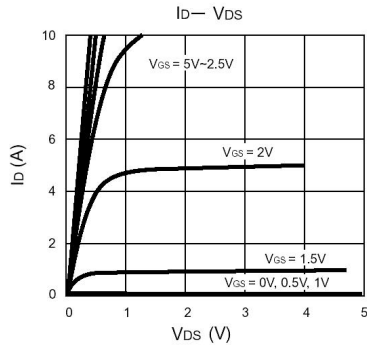
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±8	V
Drain Current – Continuous	I_D	3.0	A
Pulsed Drain Current	I_{DM}	10	A
Continuous Source Current	I_S	0.95	A
Power Dissipation	P_D	0.9	W
Storage Temperature Range	T_{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0$ $I_D=10\mu A$	20	21		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0$ $V_{DS}=20V$			1.0	μA
Gate–Body Leakage.	I_{GSS}	$V_{GS}=\pm 8V$ $V_{DS}=0V$			±100	nA
Static Drain–Source On–Resistance	$R_{DS(on)1}$	$V_{GS}=4.5V$ $I_D=3.6A$		34	60	m Ω
	$R_{DS(on)2}$	$V_{GS}=2.5V$ $I_D=3.1A$		41	115	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V$ $I_D=3.6A$		8		S
Drain–Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_D=1.25A$			1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=50\mu A$	0.50		1.0	V
State Drain Current	$I_{D(on)}$	$V_{DS}=5V$ $V_{GS}=2.5V$	4			A
Turn–On Delay Time	$t_{d(on)}$	$V_{DD}=10V$ $I_D=3.6A$ $V_{GEN}=4.5V$ $R_{GEN}=6\Omega$ $R_L=2.8\Omega$		7		ns
Turn–On Rise Time	t_r			55		
Turn–Off Delay Time	$t_{d(off)}$			15		
Turn–Off Fall Time	t_f			10		

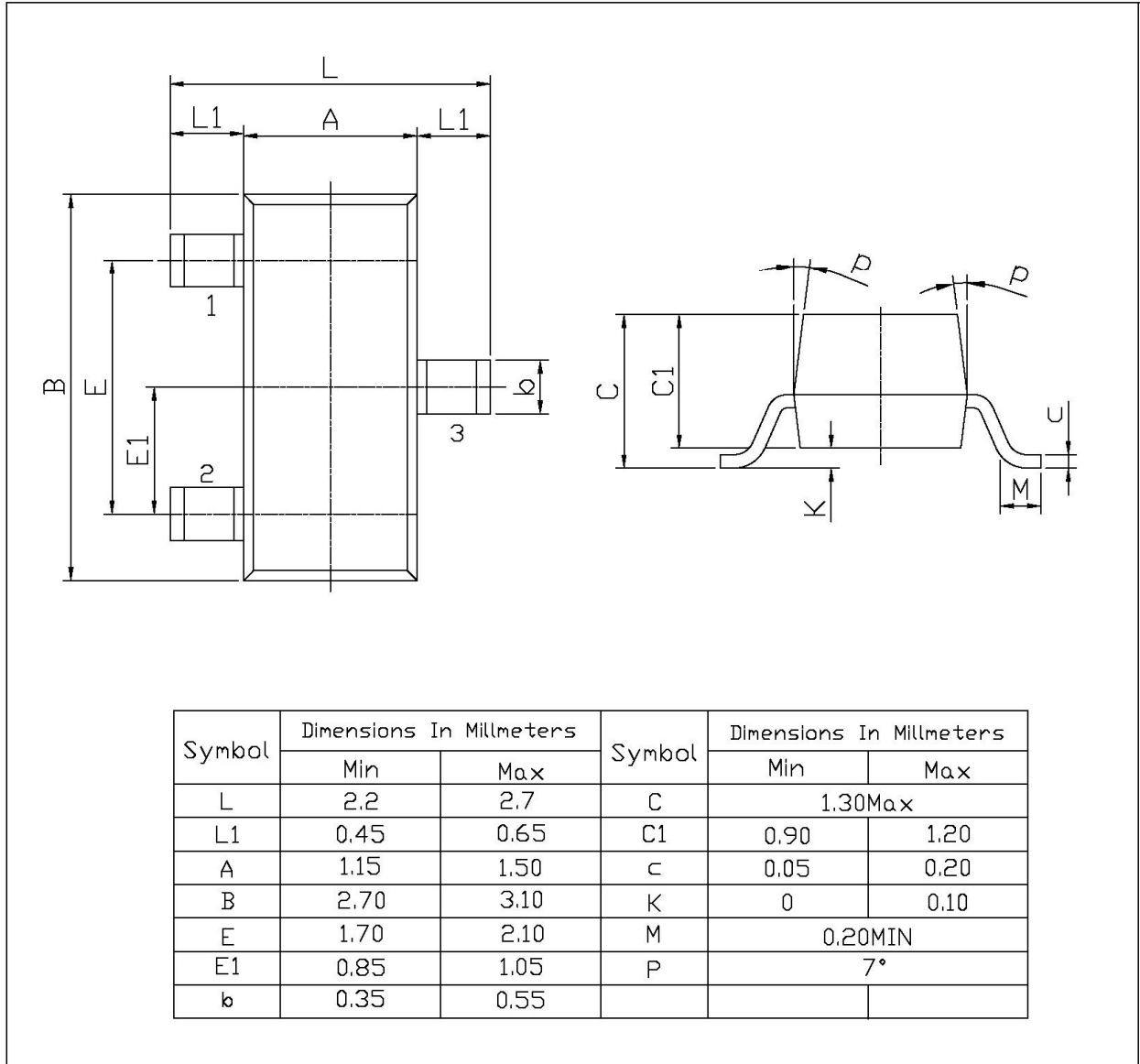
电参数曲线图 / Electrical Characteristic Curve



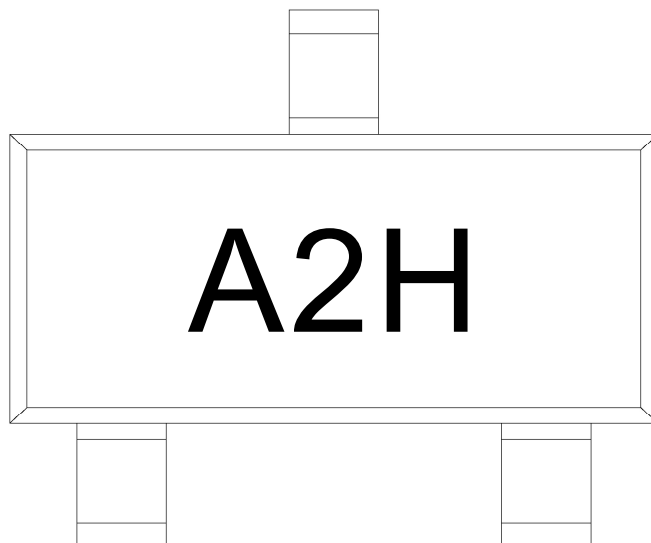
外形尺寸图 / Package Dimensions

SOT-23

单位: mm



印章说明 / Marking Instructions



说明：

A2: 为型号代码

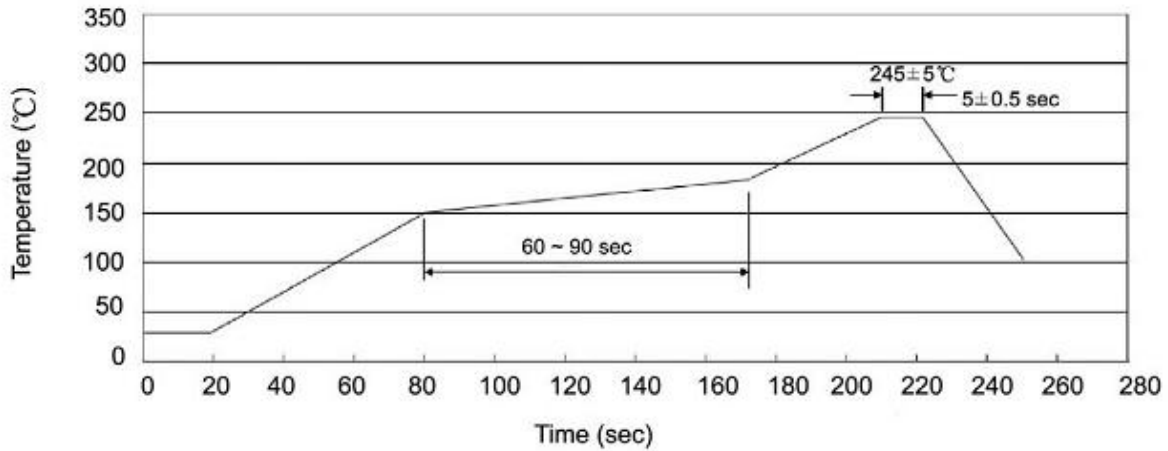
H: 为公司代码

Note:

A2 : Product Type Code

H: Company Code.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec；
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices